

1K1N65

N-C a e 600-V(D-S) P e MOSFET

RDS_{GS}^{G-} ()MAX ID
12.5 @ 10 1A

Ge e a De c :

1 65

FE

FE

DC DC

E (a e C c :

FEATURE:

F

A

Ma a (Ta=2



MOSFET ELECTRICAL CHARACTERISTICS

S a c E e c a C a a c e c (Ta = 25 °C U e O e e N e d)

Pa a e e	S b	T e C d	M	T	Ma	U
S a c						
D -	V(BR)DSS	G = 0 , D = 250 A	650			
G -	VGS(G)	D = G , D = 250 A	2		4	
G -	IGSS	D = 0 , G = 30			100	A
	IDSS	D = 650 , G = 0			10	A
D - -	RDS(GG)	G = 10 , D = 1A		9.5	12.5	
F	f GG	D = 300 , D = 1A		25		
D	VS GG	=1A, G = 0		0.8	1.5	
D a c						
	C G	D = 25 , G = 0 , = 1 H		120	150	F
	C			20	25	F
	C			3.0	4.0	F
	Q	D = 350 , G = 10 , D = 1.2A		5.0	6.0	C
G -	Q			1.0		C
G -	Q -d			2.6		C
G	R	= 1 H		10		
S c b						
- - - - - G G	d()	DD= 350 = 50 , D 1.2A, GE = 10 , = 50		5	20	
	--			25	60	
-	d(-ff)			7	25	
F	f			25	60	
D a -S ce D de C a a c e c						
B D		=1.2A, / =100A/		160		
B D	C	=1.2A, / =100A/		0.3		C
C	-D D C				1.2	A
D	C				4.8	A

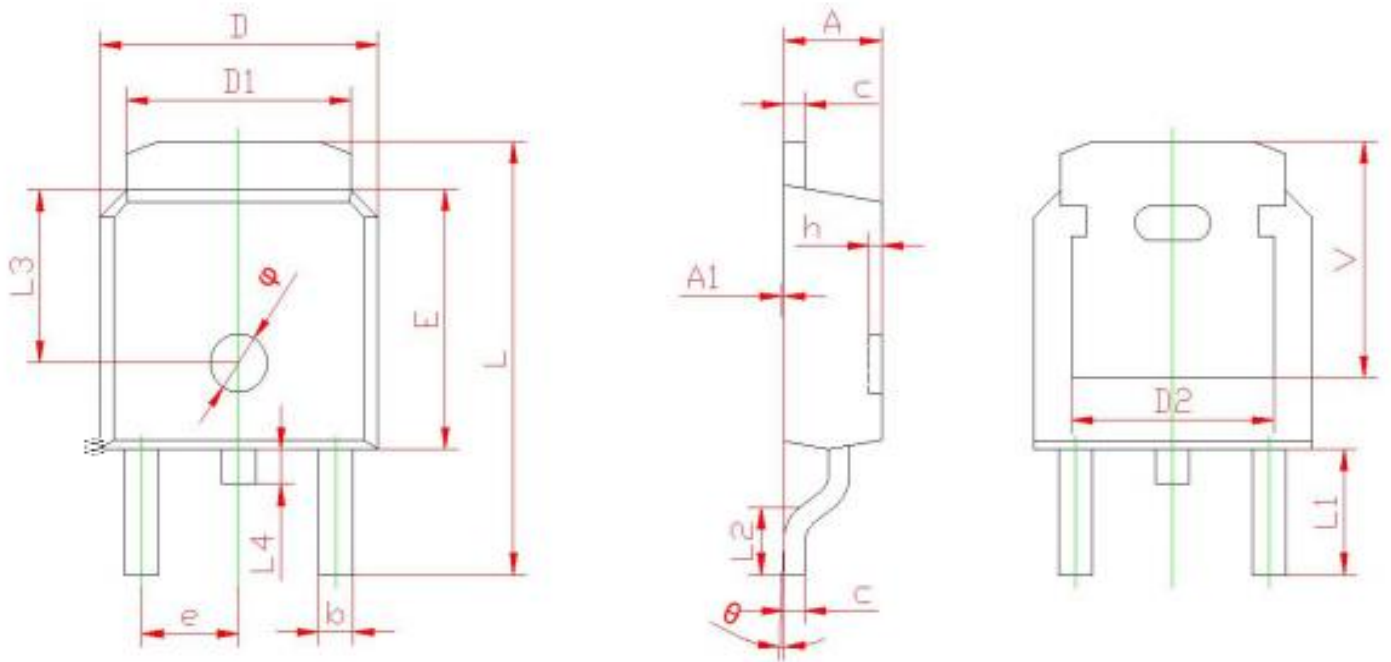
N e :

1. :
2. F 4 B , < 10 .
3. : 300 , D C 2%.
4. G



PACKAGE OUTLINE DIMENSIONS :

TO-252 PACKAGE OUTLINE DIMENSIONS

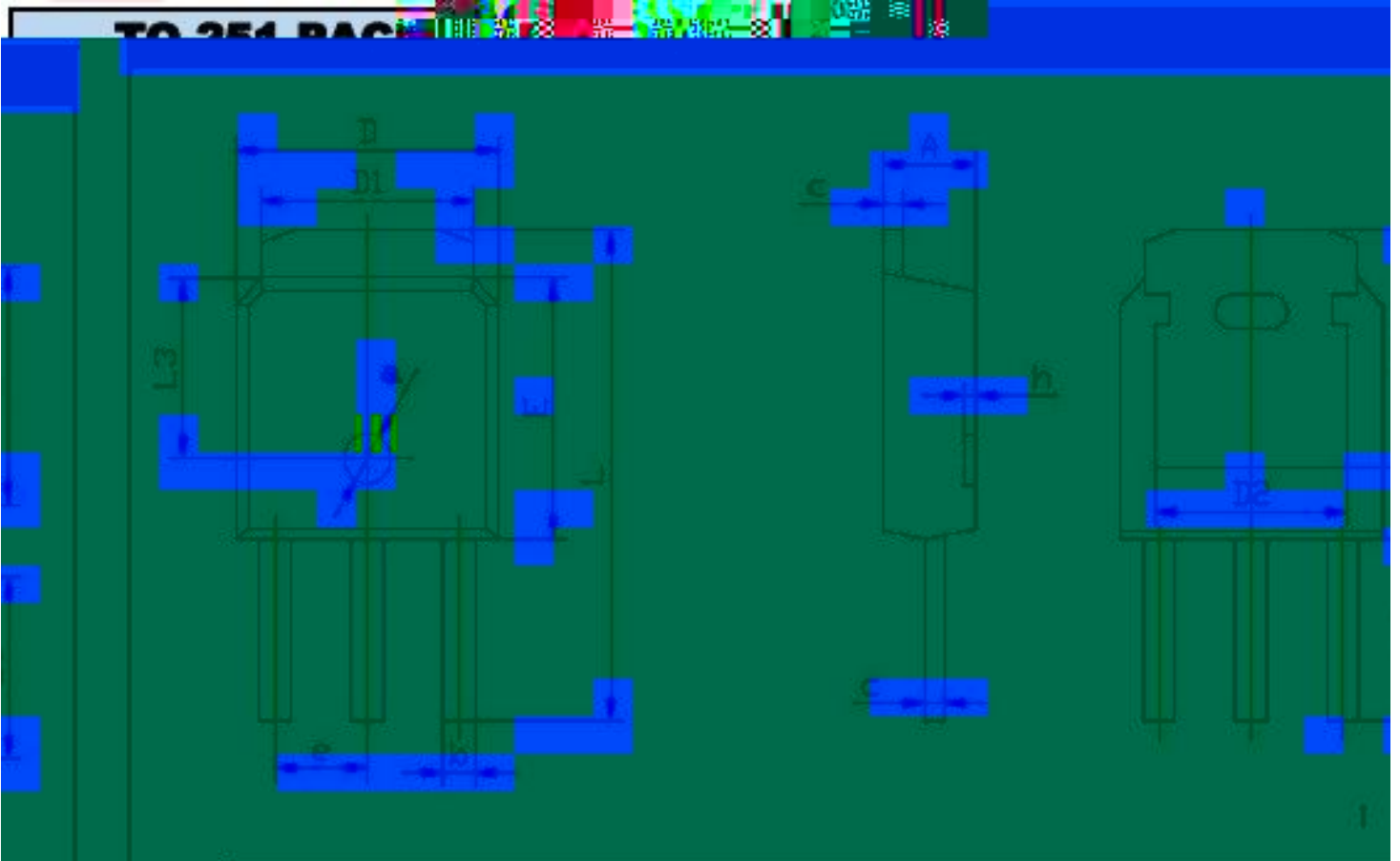


Dimensions in Millimeters

Dimensions in Inches



PACKAGE OUTLINE DIMENSIONS :



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
h	1.000	0.900	0.039	0.035
C	0.400	0.500	0.016	0.020
D	0.200	0.250	0.008	0.010
V	5.000 REF		0.217 REF	
h	0.900	0.300	0.035	0.012